

# Electronic, Mechanical, and Piezoelectric Properties of ZnO Nanowires

H. J. Xiang, Jinlong Yang,\* J. G. Hou, and Qingshi Zhu

*Hefei National Laboratory for Physical Sciences at Microscale,*

*University of Science and Technology of China, Hefei, Anhui 230026, People's Republic of China*

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Hexagonal [0001] nonpassivated ZnO nanowires are studied with density functional calculations. The band gap and Young's modulus in nanowires which are larger than those in bulk ZnO increase along with the decrease of the radius of nanowires. We find ZnO nanowires have larger effective piezoelectric constant than bulk ZnO due to their free boundary. In addition, the effective piezoelectric constant in small ZnO nanowires doesn't depend monotonously on the radius due to two competitive effects: elongation of the nanowires and increase of the ratio of surface atoms.

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ZnO[1] is one of the most important materials due to its three key advantages: semiconducting with a direct wide band gap of 3.37 eV and a large excitation binding energy (60 meV), piezoelectric due to non-central symmetry in the wurtzite structure, and biocompatible. Recently, a diversity group of ZnO nanostructures including nanowires[2], nanobelts[3], nanosprings[4], nanocombs[5], nanorings[6], nanobows[7], and nanohelices[8, 9] have been synthesized under specific growth conditions. ZnO nanostructures could have novel applications due to their unique physical and chemical properties arising from surface and quantum confinement. In particular, ZnO nanowires with relatively simple structures are important one-dimensional (1D) nanostructures. Experimentally, the group of Wang had synthesized well-aligned [0001] ZnO nanowires enclosed by facet  $\{10\bar{1}0\}$  surfaces [10, 11]. Room-temperature ultraviolet lasing[12] and piezoelectric nanogenerators based on ZnO nanowire arrays have been demonstrated[13]. Rectifying diodes of single ZnO nanobelt/nanowire-based devices [14] and a ZnO nanowire photodetector[15] were fabricated very recently.

Although many studies on ZnO nanowires have been conducted, there are some important issues remained to be addressed. First, the mechanical properties, especially the Young's modulus of ZnO nanowires are on debate in the literature[16, 17, 18, 19, 20]. For instance, Chen *et al.* [16] showed that the Young's modulus of ZnO nanowire with diameters smaller than about 120 nm is significantly higher than that of bulk ZnO. However, the elastic modulus of vertically aligned [0001] ZnO nanowires with an average diameter of 45 nm measured by atomic force microscopy was found to be far smaller than that of bulk ZnO[17]. The second issue is about the electromechanical coupling in ZnO nanowires. The effective piezoelectric coefficient of individual (0001) surface dominated ZnO nanobelts measured by piezoresponse force microscopy was found to be much larger than the value for bulk wurtzite ZnO[21]. In contrast, Fan *et al.* showed that the piezoelectric coefficient for ZnO nanopillar with

the diameter about 300 nm is smaller than the bulk values[22]. They suggested that the reduced electromechanical response might be due to structural defects in the pillars[22]. Whether the electromechanical coupling is enhanced or depressed in defect-free ZnO nanowires is not clear. Thirdly, although it is well known that the quantum confinement effect will decrease the band gap of passivated nanowires, the question that how the dangling bond in bare ZnO nanowires affects the band gap remains open. The fundamental study on these issues is crucial for developing future applications of ZnO nanowires.

In this letter, we have studied the electronic, mechanical, and piezoelectric properties of [0001] ZnO nanowires using first-principles methods for the first time. We find that the band gap increases along with the decrease of the radius of ZnO nanowires due to the radial confinement. The Young's modulus of nanowires is larger than bulk ZnO, in agreement with the experimental results of Chen *et al.*[16]. The effective piezoelectric constant in ZnO nanowires is larger than that of bulk ZnO due to the free boundary of nanowires. Moreover, the effective piezoelectric constant in small ZnO nanowires doesn't depend monotonously on the radius due to two competitive effects.

Our calculations are performed using the SIESTA package[23], a standard Kohn-Sham density-functional program using norm-conserving pseudopotentials and numerical atomic orbitals as basis sets. The local density approximation (LDA)[24] to the exchange correlation functional is employed. The DZP basis sets for both Zn and O with the energy shift parameter 20 mRy are used. The mesh cutoff parameter for real space integration is set to 350 Ry to obtain accurate atomic forces. Bulk ZnO has a wurtzite structure with the noncentral symmetry, resulting in a normal dipole moment and spontaneous polarization along the *c*-axis. The computed (experimental[25]) lattice parameters of bulk wurtzite ZnO are  $a = 3.17 \text{ \AA}$  (3.25  $\text{\AA}$ ),  $c = 5.18 \text{ \AA}$  (5.20  $\text{\AA}$ ),  $u = 0.374$  (0.381). The calculated LDA direct band gap is 0.63 eV, in good agreement with other LDA results[26, 27].

Here we mainly focus on [0001] ZnO nanowires

TABLE I: Unrelaxed diameter ( $D_0$ ) relaxed diameter ( $D$ ), relaxed lattice constant ( $c$ ), strain energy ( $E$ ), band gap ( $E_g$ ), Young's modulus ( $E_3$ ), and effective piezoelectric constant ( $e_{33}^a$ ) of five different ZnO nanowires (A, B, C, D, and E) and bulk ZnO.

|                                                     | A     | B     | C     | D     | E     | bulk  |
|-----------------------------------------------------|-------|-------|-------|-------|-------|-------|
| $D_0$ (Å)                                           | 3.66  | 9.68  | 15.96 | 22.27 | 28.59 |       |
| $D$ (Å)                                             | 3.32  | 9.32  | 15.61 | 21.97 | 28.33 |       |
| $c$ (Å)                                             | 5.335 | 5.302 | 5.270 | 5.234 | 5.215 | 5.180 |
| $E_g$ (eV)                                          | 2.40  | 1.54  | 1.09  | 0.85  | 0.75  | 0.63  |
| $E_3$ (GPa)                                         | 363   | 242   | 217   | 189   | 182   | 147   |
| $e_{33}^a$ ( $10^{-16} \mu C \text{Å}/\text{ion}$ ) | 2025  | 1837  | 1879  | 1986  | 1961  | 1453  |

since almost all ZnO nanowires grown along the [0001] direction[10, 11]. The nanowires are enclosed by six facet  $\{10\bar{1}0\}$  surfaces with low surface energy. In wurtzite bulk ZnO, each Zn (O) bonds with four O (Zn) atoms. In nanowires, the surface Zn (O) atom is only bound to three nearest neighbours. In this study, we consider only bare ZnO nanowires without saturating the surface atoms. The nanowires are modeled by hexagonal supercells whose lateral lattice constants are so large that there is almost no interaction between the nanowires. Five ZnO nanowires with diameter (Here the diameter is defined as the largest lateral distance between atoms) ranging from about 0.3 to 2.8 nm, labeled as A, B, C, D, and E respectively, are examined. The largest nanowire E contains 300 atoms in the unitcell. Since the lattice constant of small ZnO nanowires might differ significantly from the bulk counterpart, we optimize both the lattice constant  $c$  and internal coordinates of nanowires. The

relaxed structures of these ZnO nanowires are shown in Fig. 1. Since both surface Zn and O atoms move inwards and Zn atoms move much more, it looks like surface O atoms rotate outwards. The diameters of relaxed and unrelaxed nanowires are shown in Table I. We can see that the diameters of relaxed nanowires are smaller than those of unrelaxed nanowires by almost 0.3 Å. The relaxation of surface atoms in ZnO nanowires is similar to that in ZnO  $[10\bar{1}0]$  surface[28]. Along with the shrinkage of surface atoms, the lattice constant  $c$  of ZnO nanowires is increased when compared with that of bulk ZnO, as are shown in Table I. We can see that the elongation of small nanowires is considerably large, however, the lattice constants of large nanowires tend to approach that of bulk ZnO.

We have calculated the electronic structures of these ZnO nanowires. All [0001] ZnO nanowires are found to be semiconducting. Although the LDA usually underestimates the band gap, the trend of the band gaps of ZnO nanowires predicted from the LDA calculations are expected to be correct. The LDA band gaps are shown in Table I. Clearly, the band gaps of ZnO nanowires increase monotonously along with the decrease of the radius of nanowires. In comparison with bulk ZnO, the increment of the band gap of nanowire A can be as large as 1.77 eV. The blueshift of the band gap should be due to the quantum confinement effect. However, the gap-broadening effect in nonpassivated nanowires is unusual. For example, nonpassivated Si nanowires grown along the  $\langle 100 \rangle$  direction are found to be metallic and semimetallic due to the presence of surface states[29]. To see the details of the electronic structure of ZnO nanowires, we plot the band structure of nanowire B in Fig. 2(a). The band structures of other ZnO nanowires are similar to that of nanowire B. Clearly, ZnO nanowires have a direct gap at  $\Gamma$ . To gain an insight into the character of the lowest unoccupied molecular orbital (LUMO) and highest occupied molecular orbital (HOMO), we show the charge density of the LUMO and HOMO states at  $\Gamma$  in Fig. 2(b) and (c), respectively. We can see that the LUMO is delocalized in the whole nanowire, indicating that it is a bulk state instead of a surface state. The delocalized distribution is also responsible for the large dispersion of the LUMO from  $\Gamma$  to A. Furthermore, due to the delocalized character, the LUMO energy will increase substantially in small radius nanowires due to the radial confinement. Since the charge density of the HOMO at  $\Gamma$  mainly contributed by surface atoms, the HOMO is a surface state. The HOMO at  $\Gamma$  lies only 80 meV above the top of valence band of bulk ZnO, and its position changes little in nanowires with different diameters since the HOMO is mainly composed by surface O 2p like dangling bonds. The HOMO is similar to the P1 surface state in the ZnO  $(10\bar{1}0)$  surface as identified by Schröer *et al.*[28]. It is the different response to the radial confinement between the LUMO and HOMO that leads to the overall gap-

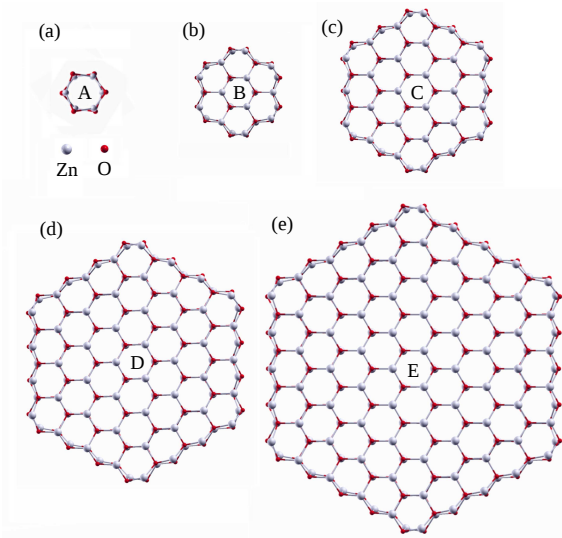


FIG. 1: (Color online) Relaxed structures for ZnO nanowires with different radius. We label these nanowires as A, B, C, D, and E.

broadening effect in ZnO nanowires.

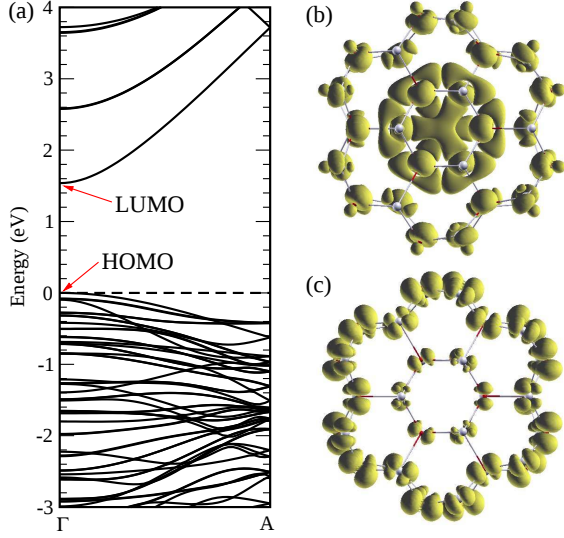


FIG. 2: (Color online) (a) The band structure of nanowire B. (b) The charge density of the LUMO state at  $\Gamma$  for nanowire B. (c) The charge density of the HOMO state at  $\Gamma$  for nanowire B.

Now we turn to study the mechanical properties of ZnO nanowires. An important mechanical parameter for describing a one-dimensional system is the Young's modulus. We calculate  $E_3$  in the [0001] direction by using the following formula:

$$E_3 = \frac{1}{V} d^2 E / d\epsilon^2, \quad (1)$$

where  $E$  is the total energy,  $\epsilon$  is the axial strain, and  $V$  is the system volume. For nanowires, we define the volume as  $V = S \times c$ , where  $S$  is the area of the cross section of the nanowire and  $c$  is the lattice constant. For each nanowire, we perform seven calculations with  $\epsilon$  range from  $-3\%$  to  $3\%$ . In each calculations for the nanowires, we fully relaxed the internal coordinates. To compare our results for nanowires with bulk ZnO, we also calculate the Young's modulus of bulk ZnO. In the calculations, only the lattice constant  $c$  is fixed to the strained value, all other degrees of freedom including the lateral lattice constants are optimized. Our results for bulk ZnO and ZnO nanowires are reported in Table I. The calculated Young's modulus of bulk ZnO is 147 GPa, which is close to the value 140 GPa deduced from the experimental elastic constants[30]. For ZnO nanowires, the Young's modulus increase monotonously along with the decrease of the radius of nanowires and are larger than that of bulk ZnO. To estimate the Young's modulus of larger ZnO nanowires, the calculated results are fitted using  $E_3(D) = 145.87 + 1172.63D^{-1} - 1477.58D^{-2} + 4830.55D^{-3}$ , where Young's modulus  $E_3$  is in unit of GPa and diameter  $D$  is in unit of  $\text{\AA}$ . The trend of Young's modulus accords qualitatively with the

experimental results[16]. Our results also agree qualitatively with the Young's modulus of ZnO nanobelts with rectangular cross-sections in the [0001] orientation calculated from empirical molecular dynamics simulations[20]. However, the experimental Young's modulus of ZnO nanowires are significantly larger than our results. For example, the Young's modulus of a ZnO nanowire with the diameter 20 nm estimated using their fitted formula is 202 GPa, however, our value estimated from the fitted formula is only 152 GPa. The reason for the discrepancy is not very clear.

Before we proceed to discuss the piezoelectric effect in ZnO nanowires, we first calculate piezoelectric constant  $e_{33}$  of bulk ZnO. The piezoelectric constants  $e_{ij}$  is defined as follows:  $e_{ij} = \partial \mathbf{P}_i / \partial \epsilon_j$ , where  $\mathbf{P}$  is the total polarization, and  $\epsilon_j$  is the strain tensor component. Here, the piezoelectric constants are computed by combining the Berry phase method in the modern theory of polarization[31] with the finite difference method. The piezoelectric effect in tetrahedrally bonded semiconductors results from two different terms of opposite sign: The "clamped-ion" and the "internal-strain" contributions. The calculated clamped-ion and relaxed-ion piezoelectric constant  $e_{33}$  for bulk ZnO is  $-0.77$  and  $1.29 \text{ C/m}^2$  respectively, which accords with others' results ( $-0.75$  and  $1.28 \text{ C/m}^2$ )[26].

As the conventional definition of piezoelectric constant for three-dimensional bulk is not appropriate for describing the piezoelectric properties of one-dimensional systems, we define the atomic averaged effective piezoelectric constant as:  $e_{33}^a = e_{33} \times V_{\text{scell}} / N$ , where  $N$  is the number of atoms, and  $V_{\text{scell}}$  is the volume of the supercell. The results are presented in Fig. 3(a) and Table I. We can clearly see that  $e_{33}^a$  of nanowires is considerably larger than that of bulk ZnO. We find that larger  $e_{33}^a$  in nanowires is caused by the free boundary of nanowires. In the calculations of  $e_{33}^a$ , the lateral lattice constants are fixed. When bulk ZnO is strained along the  $c$  axis, atoms can not relaxed freely along the lateral directions. However, when nanowires are compressed or elongated along the  $c$  axis, atoms can relaxed freely along the lateral directions due to the free boundary. Hence, the effective piezoelectric constant  $e_{33}^a$  in nanowires should approach  $e_{33}^b - 2e_{31}^b \times \nu$ , where  $e_{33}^b$  and  $e_{31}^b$  is effective piezoelectric constants of bulk ZnO,  $\nu = -\epsilon_1 / \epsilon_3 = -\epsilon_2 / \epsilon_3$  is Poisson's ratio ( $\epsilon_1 = \epsilon_2 = (a - a_0) / a_0$ ,  $\epsilon_3 = (c - c_0) / c_0$ ,  $a$  is the relaxed lateral lattice constant when the lattice constant of ZnO is changed to  $c$ ). Since  $\nu > 0$  and  $e_{31}^b < 0$ [26],  $e_{33}^a$  in nanowires is larger than  $e_{33}^b$ . For the same reason, effective piezoelectric coefficient in ZnO nanobelts was also found experimentally to be larger than that of bulk ZnO by Zhao *et al.*[21]. One might expect smaller nanowires have larger piezoelectric constant due to their larger ratio of surface atoms. However, Fig. 3(a) shows that  $e_{33}^a$  doesn't monotonously depend on the radius of ZnO nanowires:  $e_{33}^a$  for nanowire D is larger than that

for nanowire C and E. We attribute this anormal behavior to the increase of the lattice constant along with the decrease of the radius of ZnO nanowires, since the piezoelectric constant of a certain nanowire decreases along with the increase of the lattice constant  $c$ , as shown in Fig. 3(b). In fact, we also calculate the effective piezoelectric constant of the nanowires with bulk lattice constant  $c$ , and the results (also shown in Fig. 3(a)) indicate a monotonous decreasing dependence of  $e_{33}^a$  upon the radius of nanowires. From Fig. 3(a), we can also see that the difference of  $e_{33}^a$  between nanowires D and E with the lattice constant  $c$  relaxed or fixed is very small, suggesting that larger nanowires will have similar  $e_{33}^a$  as nanowire E.

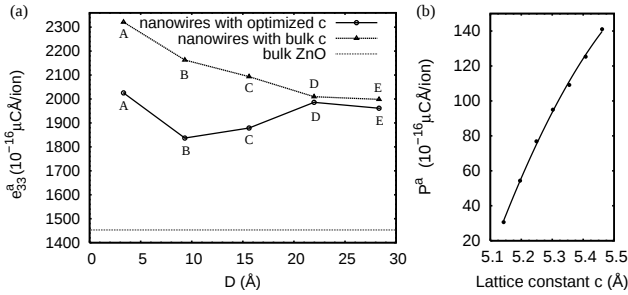


FIG. 3: (a) The dependence of the effective piezoelectric constant  $e_{33}^a$  upon the diameters of the nanowires with optimized lattice constant  $c$  and nanowires with bulk lattice constant  $c$ . The horizontal dotted line indicates the piezoelectric constant of bulk ZnO. (b) shows the polarization of ZnO nanowire B with different  $c$ .

To summarize, we have carried out comprehensive first-principles studies on [0001] ZnO nanowires. The band gaps of ZnO nanowires increase along with the decrease of the radius of nanowires due to the quantum confinement effect. The Young's modulus of thinner nanowires is larger than that of thicker nanowires. Our calculations indicate that the effective piezoelectric constant  $e_{33}^a$  of ZnO nanowires is larger than that of bulk ZnO. In addition, we find a non-trivial dependence of the electromechanical coupling of ZnO nanowires upon the radius as a result of the competition between two opposite factors. Our results support the application of ZnO nanowires as nanosensors and nanoactuators.

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\* Corresponding author. E-mail: jlyang@ustc.edu.cn

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